NOT RECOMMENDED FOR NEW DESIGN
USE DMP3068L

Lead-free Green

DMP3130L

P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D T_A = +25°C
-30V	77mΩ@ V_{GS} = -10V	-3.5A
	95mΩ@ V_{GS} = -4.5V	-3.0A
	150mΩ@ V_{GS} = -2.5V	-2.4A

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet (DMP3130LQ)**

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power Management Functions
- Analog Switch

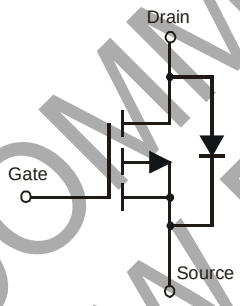
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

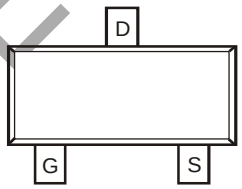
SOT23



Top View



Equivalent Circuit



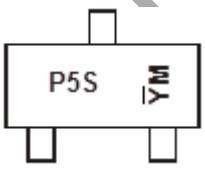
Top View

Ordering Information (Note 4)

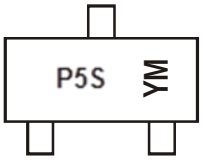
Part Number	Case	Packaging
DMP3130L-7	SOT23	3000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Chengdu A/T Site



Shanghai A/T Site

P5S = Product Type Marking Code
YM = Date Code Marking for SAT (Shanghai Assembly/ Test Site)
$\overline{Y}$M = Date Code Marking for CAT (Chengdu Assembly/ Test Site)
Y or $\overline{Y}$ = Year (ex: E = 2017)
M = Month (ex: 9 = September)

Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017	2018
Code	V	W	X	Y	Z	A	B	C	D	E	F

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

© Diodes Incorporated

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Drain Current (Note 5) V_{GS} = -4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	-3.0 -2.6	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	-4.1 -3.2	A
Maximum Continuous Body Diode Forward Current (Note 5)			I_S	-1.6	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	-20	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	0.7	W
	T_A = +70°C		0.4	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	184	°C/W
	t<10s		115	
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	1.3	W
	T_A = +70°C		0.8	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	94	°C/W
	t<10s		61	
Thermal Resistance, Junction to Case		$R_{\theta JC}$	25	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	µA	V_{DS} = -30V, V_{GS} = 0V
Gate-Body Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±12V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.6	—	-1.3	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	59	77	mΩ	V_{GS} = -10V, I_D = -4.2A
		—	73	95		V_{GS} = -4.5V, I_D = -4A
		—	115	150		V_{GS} = -2.5V, I_D = -3A
Forward Transconductance	g_{fs}	—	8	—	S	V_{DS} = -5V, I_D = -4A
Source-Drain Diode Forward Voltage	V_{SD}	—	-0.8	-1.25	V	V_{GS} = 0V, I_S = -3.0A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	432	864	pF	V_{DS} = -15V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	87	174	pF	
Reverse Transfer Capacitance	C_{rss}	—	62	124	pF	
Gate Resistance	R_G	—	4.04	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
SWITCHING CHARACTERISTICS (Note 8)						
Total Gate Charge	Q_G	—	5.9	11.8	nC	V_{DS} = -15V, V_{GS} = -4.5V, I_D = -4.0A
		—	12	24		V_{DS} = -15V, V_{GS} = -10V, I_D = -4.0A
Gate-Source Charge	Q_{GS}	—	1.0	2.0		V_{DS} = -15V, V_{GS} = -4.5V, I_D = -4.0A
Gate-Drain Charge	Q_{GD}	—	3.1	6.2		
Turn-On Delay Time	$t_{D(ON)}$	—	4.6	9.2	ns	V_{DS} = -15V, V_{GS} = -10V, I_D = -1A, R_G = 6.0Ω
Rise Time	t_R	—	6.5	13.0		
Turn-Off Delay Time	$t_{D(OFF)}$	—	27.8	55.6		
Fall Time	t_F	—	15.0	30.0		

Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

NOT RECOMMENDED FOR NEW DESIGN

© Diodes Incorporated

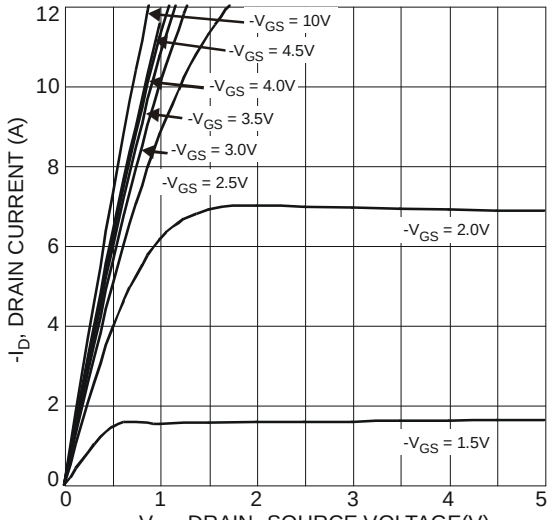


Fig. 1 Typical Output Characteristics

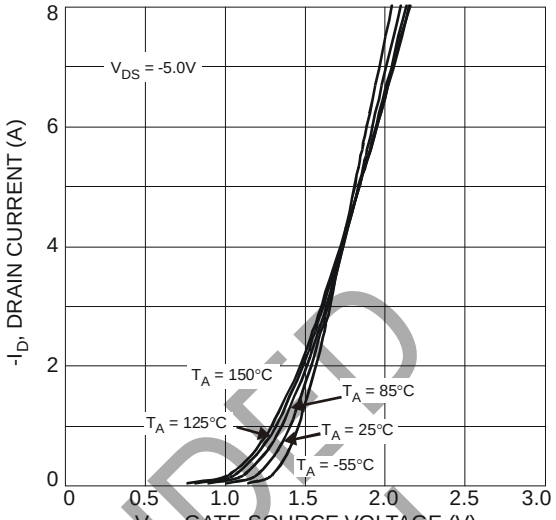


Fig. 2 Typical Transfer Characteristics

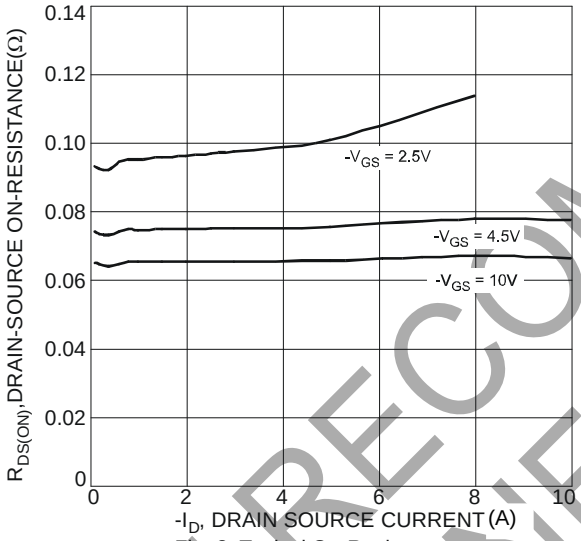


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

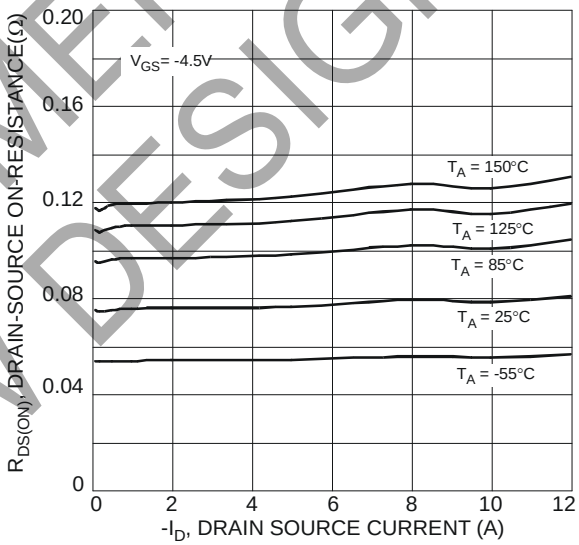


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

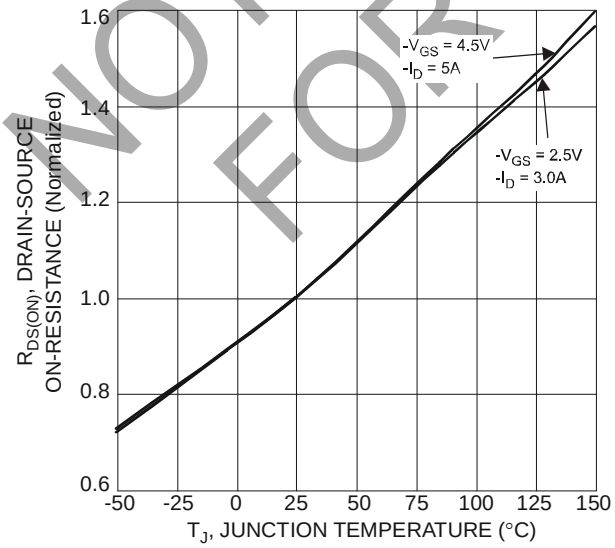


Fig. 5 On-Resistance Variation with Temperature

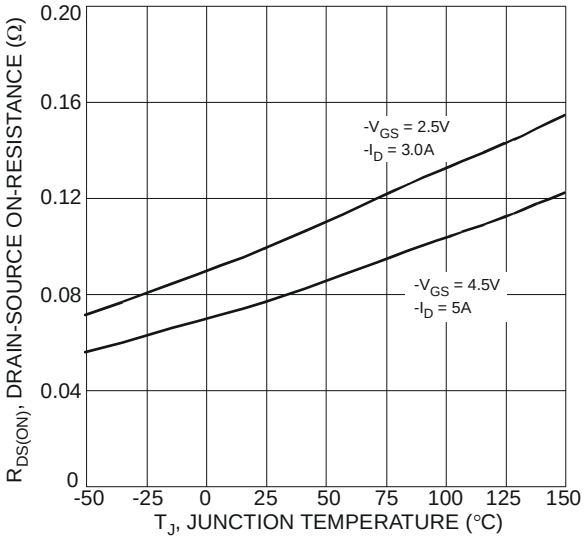


Fig. 6 On-Resistance Variation with Temperature

NOT RECOMMENDED FOR NEW DESIGN

© Diodes Incorporated

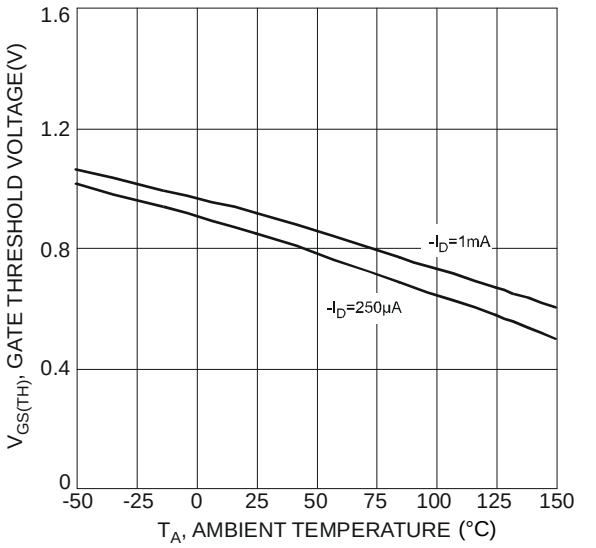


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

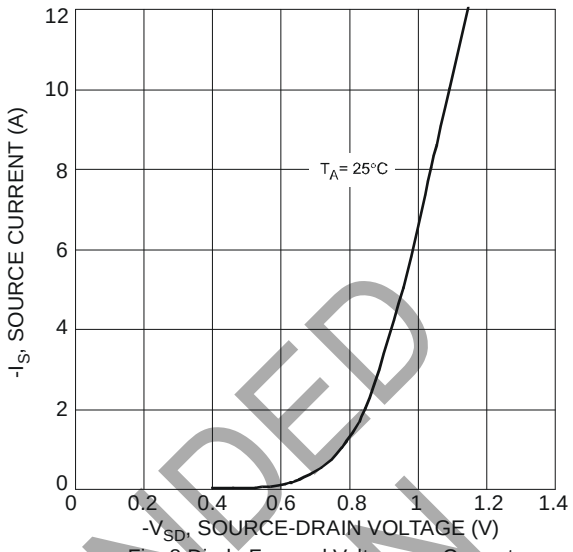


Fig. 8 Diode Forward Voltage vs. Current

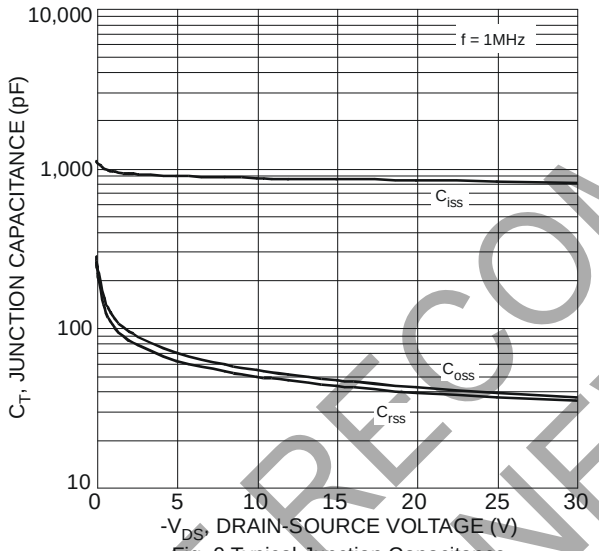


Fig. 9 Typical Junction Capacitance

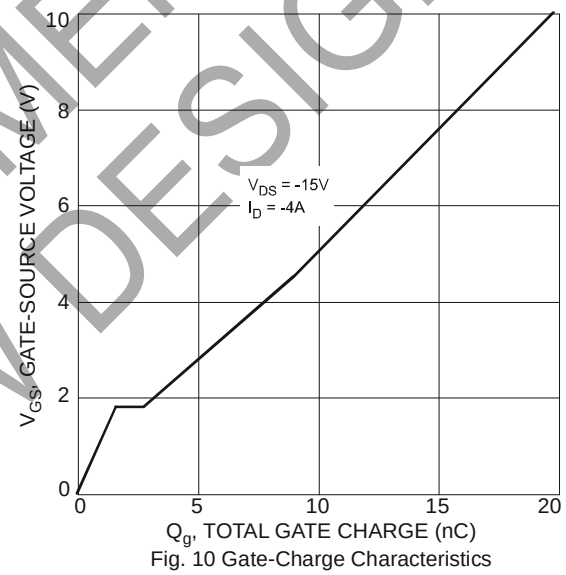


Fig. 10 Gate-Charge Characteristics

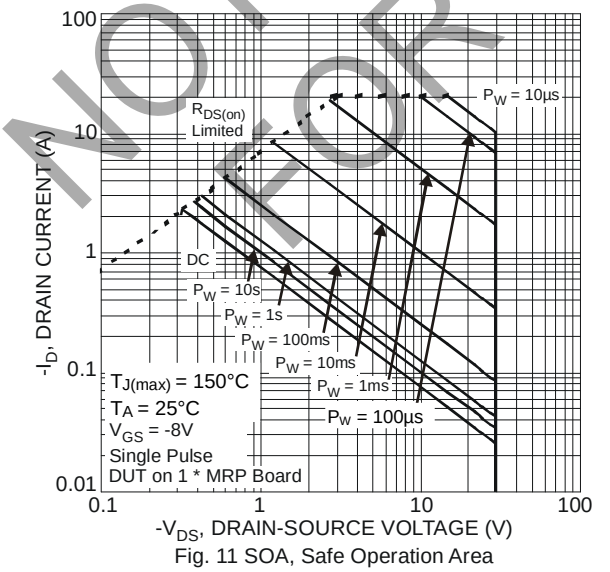


Fig. 11 SOA, Safe Operation Area

NOT RECOMMENDED FOR NEW DESIGN

© Diodes Incorporated

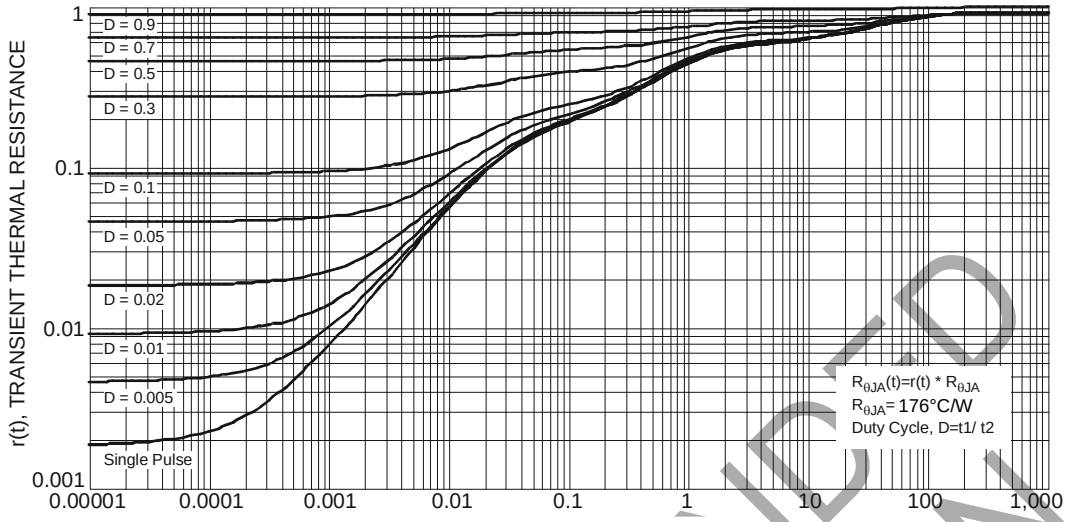


Fig. 12 Transient Thermal Resistance

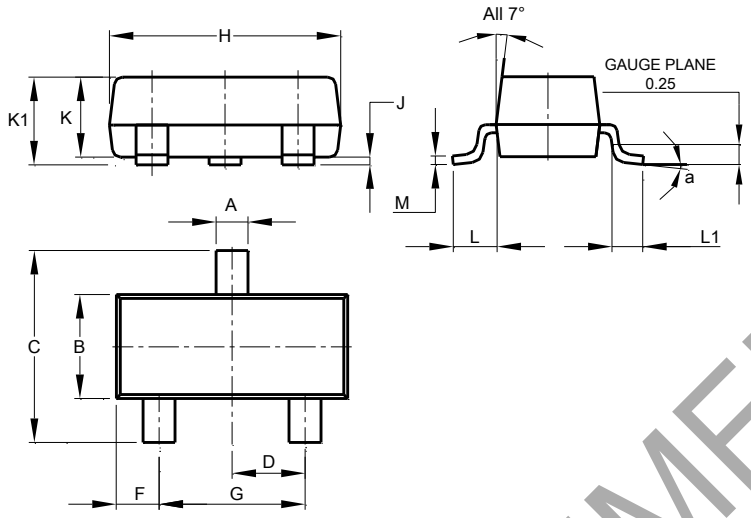
NOT RECOMMENDED FOR NEW DESIGN

© Diodes Incorporated

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

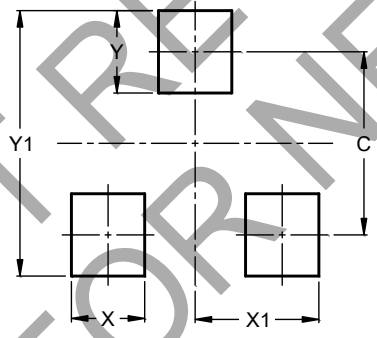


SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

NOT RECOMMENDED FOR NEW DESIGN

© Diodes Incorporated

IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

A. Life support devices or systems are devices or systems which:

1. are intended to implant into the body, or
2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2017, Diodes Incorporated

www.diodes.com

NOT RECOMMENDED FOR NEW DESIGN

ENTEGRECİ

Bu belge www.entegreci.com üzerinden sunulmaktadır.

Elektronik komponent tedarikinde Entegreci

Entegreci, Eskişehir merkezli, Türkiye geneline satış yapan bir elektronik komponent mağazasıdır. Entegreler (IC), mikrodenetleyiciler, transistörler, diyotlar, pasif elemanlar, konnektörler, modüller ve geliştirme kartları tek adetten seri üretim adetlerine kadar satılır. Ürün sayfalarında güncel stok durumunu, fiyatı ve datasheet bağlantısını bulabilirsiniz.

Parça koduyla arama

Üretici parça numarasını yazın; stok ve fiyatı hemen görün.

www.entegreci.com

Ürün kategorileri

Entegreden kapasitöre tüm elektronik komponent kategorileri.

Kategorilere göz atın

Üreticiler

Aradığınız üreticinin ürünlerini tek sayfada inceleyin.

Üreticileri görün

Toplu alım ve teklif

Listede olmayan ya da yüksek adetli parçalar için teklif isteyin.

Teklif isteyin

www.entegreci.com | **destek@entegreci.com** | **0850 305 90 34**

Entegreci is an online electronic components store based in Türkiye. Search by manufacturer part number to see stock, prices and datasheets for integrated circuits, microcontrollers, transistors, passive components and connectors, or request a quote for parts that are not listed.

Bu sayfa Entegreci tarafından eklenmiştir. Belgenin önceki sayfaları asıl yayıncısına aittir ve içeriği değiştirilmemiştir; en güncel sürüm için belgenin yayıncısına başvurun.